



# WIDEBAND HIGH GAIN POWER AMPLIFIER MODULE, 2 - 20 GHz

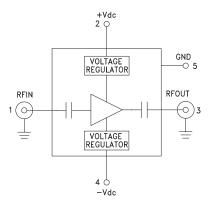


## **Typical Applications**

The HMC-C026 Wideband PA is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military & Space
- Test Instrumentation
- Fiber Optics

## **Functional Diagram**



#### **Features**

Gain: 31 dB @ 6 GHz

P1dB Output Power: +26 dBm @ 6 GHz

Noise Figure: 2.5 dB @ 8 GHz

Spurious-Free Operation

Regulated Supply and Bias Sequencing

Hermetically Sealed Module

Field Replaceable SMA connectors

-55 °C to +85 °C Operating Temperature

# **General Description**

The HMC-C026 is a GaAs MMIC pHEMT Distributed Power Amplifier in a miniature, hermetic module with replaceable SMA connectors which operates between 2 and 20 GHz. The amplifier provides 31 dB of gain, 2.5 dB noise figure, +30 dBm output IP3 and up to +26 dBm of output power at 1 dB gain compression. The wideband amplifier I/Os are internally matched to 50 Ohms and are DC blocked making the HMC-C026 ideal for EW, ECM RADAR and test equipment applications. Integrated voltage regulators allow for flexible biasing of both the negative and positive supply pins, while internal bias sequencing circuitry assures robust operation.

# Electrical Specifications, $T_{\Delta} = +25^{\circ}$ C, +Vdc = +11V to +16V, -Vdc = -3V to -12V

Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range	2 - 6		6 - 12		12 - 16		16 - 20			GHz			
Gain	28	31		26	29		24	27		19	22		dB
Gain Flatness		±0.25			±0.75			±1.0			±2.0		dB
Gain Variation Over Temperature		0.03	0.04		0.03	0.04		0.03	0.04		0.03	0.04	dB/ °C
Noise Figure		3.0	5.0		2.5	3.5		3.0	4.0		3.5	5.0	dB
Input Return Loss		15			15			13			10		dB
Output Return Loss		15			15			10			8		dB
Output Power for 1 dB Compression (P1dB)	23	26		22.5	25.5		20	24		18	21		dBm
Saturated Output Power (Psat)		27.5			27			25			23		dBm
Output Third Order Intercept (IP3)		33			30			27			24		dBm
Positive Supply Current (+IDC)		400	450		400	450		400	450		400	450	mA
Negative Supply Current (-IDC)		3.2	5		3.2	5		3.2	5		3.2	5	mA

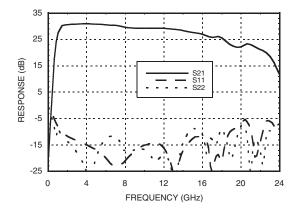
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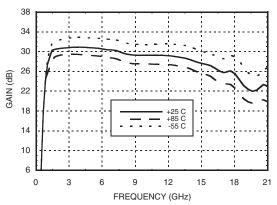


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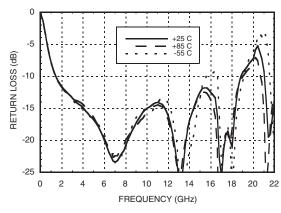
#### Gain & Return Loss



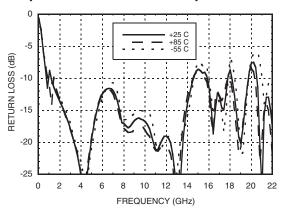
## Gain vs. Temperature



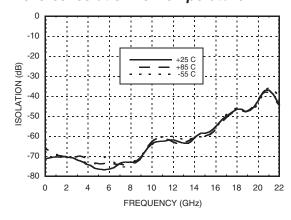
## Input Return Loss vs. Temperature



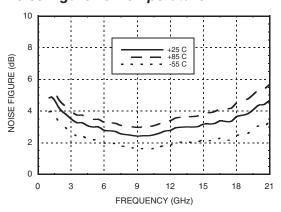
### **Output Return Loss vs. Temperature**



### Reverse Isolation vs. Temperature



### Noise Figure vs. Temperature



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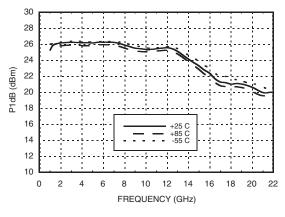
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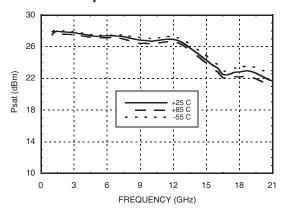


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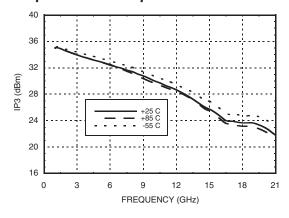
## P1dB vs. Temperature



### Psat vs. Temperature



### Output IP3 vs. Temperature



# **Absolute Maximum Ratings**

RF Input Power (RFIN)	+23 dBm		
Positive Bias Supply Voltage (+Vdc)	+17V Max		
Negative Bias Supply (-Vdc)	-16V Min.		
Thermal Resistance (at +Vdc = 12V, -Vdc = -4V, DC Power = 4.8 Watts)	15.9 °C/W		
Storage Temperature	-65 to +150 °C		
Operating Temperature	-55 to +85 °C		







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### **Pin Descriptions**

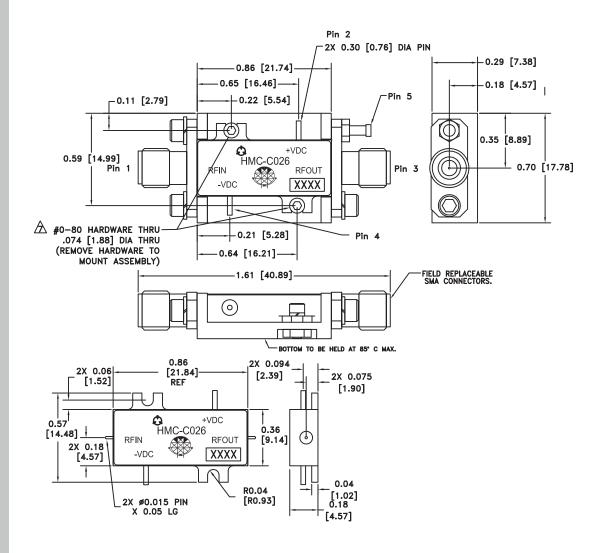
Pin Number	Function	Description	Interface Schematic		
1	RFIN & RF Ground	RF input connector, SMA female, field replaceable. This pin is AC coupled and matched to 50 Ohms.	RFIN 0——   —— —— —— —— —— —— —— —— —— —— —— ——		
2	+Vdc	Positive power supply voltage for the amplifier.	+Vdc O VOLTAGE REGULATOR		
3	RFOUT & RF Ground	RF output connector, SMA female. This pin is AC coupled and matched to 50 Ohms.			
4	-Vdc	Negative power supply voltage for the amplifier	-Vdc O VOLTAGE RESULATOR =		
5	GND	Power supply ground.	GND =		





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### **Outline Drawing**



## Package Information

•			
Package Type	C-3B		
Package Weight [1]	12 gms <sup>[2]</sup>		
Spacer Weight	N/A		

- [1] Includes the connectors
- [2] ±1 gms Tolerance

#### NOTES:

- 1. PACKAGE, LEADS, COVER MATERIAL: KOVAR™
- 2. SPACER MATERIAL: ALUMINUM
- 3. PLATING: ELECTROLYTIC GOLD 50 MICROINCHES MIN., OVER ELECTROLYTIC NICKEL 75 MICROINCHES MIN.
- 4. ALL DIMENSIONS ARE IN INCHES [MILLIMETERS].
- 5. TOLERANCES ±.005 [0.13] UNLESS OTHERWISE SPECIFIED.
- 6. FIELD REPLACEABLE SMA CONNECTORS. TENSOLITE 5602 5CCSF OR EQUIVALENT.
- ↑ TO MOUNT MODULE TO SYSTEM PLATFORM REPLACE 0 -80 HARDWARE WITH DESIRED MOUNTING SCREWS.



RoHS V

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Notes:

**AMPLIFIERS**